



BC303

BC304

PNP SILICON AF MEDIUM POWER AMPLIFIERS & SWITCHES

CASE TO-39

THE BC303, BC304 ARE PNP SILICON PLANAR EPITAXIAL TRANSISTORS RECOMMENDED FOR AF DRIVERS & OUTPUTS, AS WELL AS FOR SWITCHING APPLICATIONS UP TO 1 AMPERE. THEY ARE COMPLEMENTARY TO THE NPN TYPE BC300, BC301, BC302.



ABSOLUTE MAXIMUM RATINGS

		BC303	BC304
Collector-Base Voltage	-V _{CB0}	85V	60V
Collector-Emitter Voltage	-V _{CE0}	60V	45V
Emitter-Base Voltage	-V _{EB0}	7V	7V
Collector Current	-I _C	1A	
Total Power Dissipation (T _C ≤ 25°C)	P _{tot}	6W	
		850mW	
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to 175°C	

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	-LV _{CEO} *					-I _C =100mA I _B =0
		BC303	60			V
		BC304	45			V
Collector-Emitter Breakdown Voltage	-LV _{CEV}					-I _C =100mA -V _{EB} =1.5V
		BC303 only	85			V
Collector Cutoff Current	-I _{CBO}			20	nA	-V _{CB} =60V I _E =0
Emitter Cutoff Current	-I _{EBO}			20	nA	-V _{EB} =5V I _C =0
Collector-Emitter Saturation Voltage	-V _{CE(sat)} *		0.1	0.65	V	-I _C =150mA -I _B =15mA
Base-Emitter Voltage	-V _{BE} *		0.78		V	-I _C =150mA -V _{CE} =10V
D.C. Current Gain	H _{FE} *		20			-I _C =0.1mA -V _{CE} =10V
			40	240		-I _C =150mA -V _{CE} =10V
			20			-I _C =500mA -V _{CE} =10V
D.C. Current Gain	H _{FE} *	Group 4	40	80		-I _C =150mA -V _{CE} =10V
		Group 5	70	140		
		Group 6	120	240		
Current Gain-Bandwidth Product	f _T		100		MHz	-I _C =10mA -V _{CE} =10V
Collector-Base Capacitance	C _{ob}		17		pF	-V _{CB} =10V I _E =0 f=1MHz

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%

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TYPICAL CHARACTERISTICS

